



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

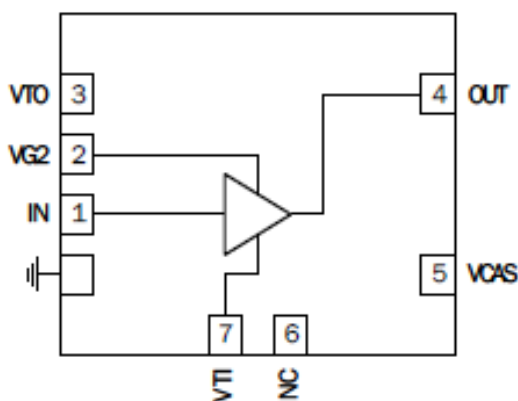
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



SDA-5000

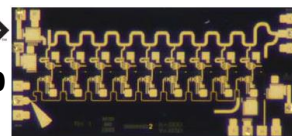
GaAs Distributed Amplifier

RFMD's SDA-5000 is a directly coupled (DC) GaAs microwave monolithic integrated circuit (MMIC) distributed driver amplifier designed to support a wide array of high frequency commercial, military, and space applications. They are ideal for wideband amplifier gain blocks, broadband test equipment (ATE), military, and aerospace applications.



Functional Block Diagram

rfmd
SDA-5000



Package: Die, 2.2mm x 1.45mm x 0.102mm

Features

- DC to 35GHz Operation
- +17dBm P_{3dB}
- Gain = 11.8dB Typical
- Noise Figure = 4dB
- Output Voltage to 8V_{pp}
- 100mA Total Current

Applications

- Instrumentation
- Military
- Aerospace
- Broadband ATE

Ordering Information

SDA-5000	GaAs Distributed Amplifier, GelPak, 10 pieces or more
SDA-5000SB	GaAs Distributed Amplifier, GelPak, 2 pieces

Absolute Maximum Ratings

Parameter	Rating	Unit
Drain Bias Voltage (V_{DD})	+8.0	V_{DC}
Gate Bias Voltage (V_{T1})	-2 to +0	V_{DC}
Gate Bias Voltage (V_{G2})	$(V_{DD}-8.0) V_{DC}$ to V_{DD}	V
RF Input Power ($V_{DD} = +8.0V_{DC}$)	15	dBm
Operating Junction Temperature (T_J)	+175	°C
Continuous Power Dissipation ($T = +85^{\circ}\text{C}$)	750	mW
Thermal Resistance (Pad to Die Bottom)	116	°C/W
Storage Temperature	-40 to +150	°C
Operating Temperature	-40 to +85	°C
ESD JESD22-A114 Human Body Model (HBM)	Class 0 (All Pads)	



Caution! ESD sensitive device.



RFMD Green: RoHS compliant per EU Directive 2011/65/EU, halogen free per IEC 61249-2-21, <1000ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony solder.

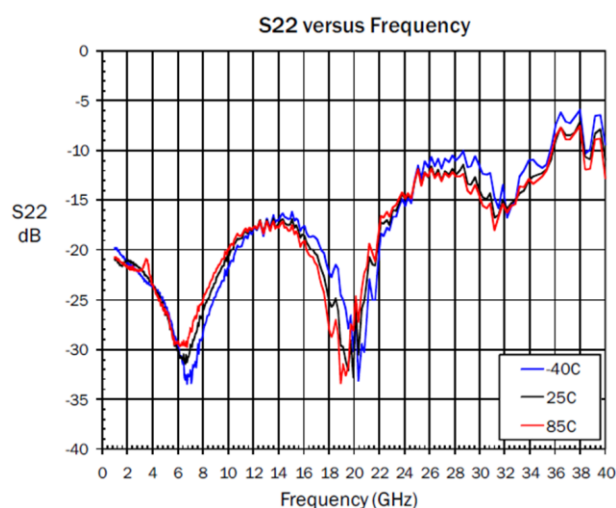
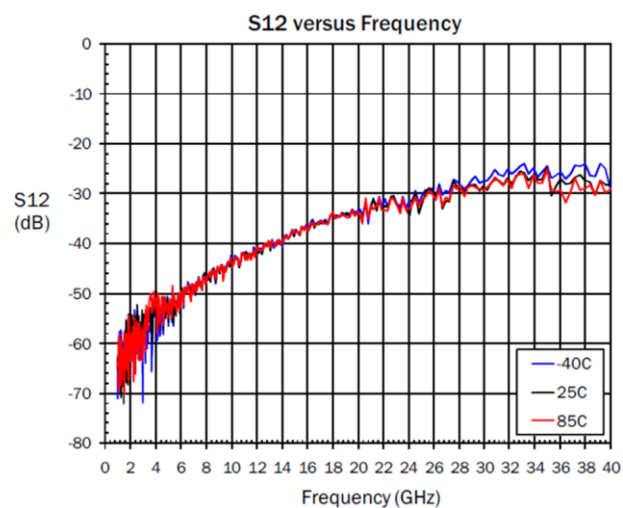
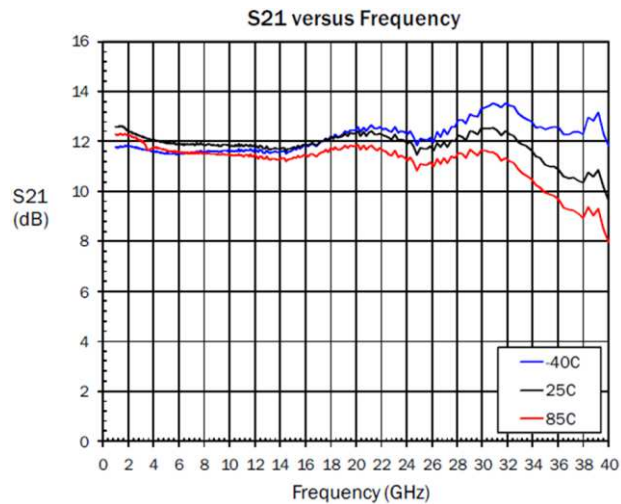
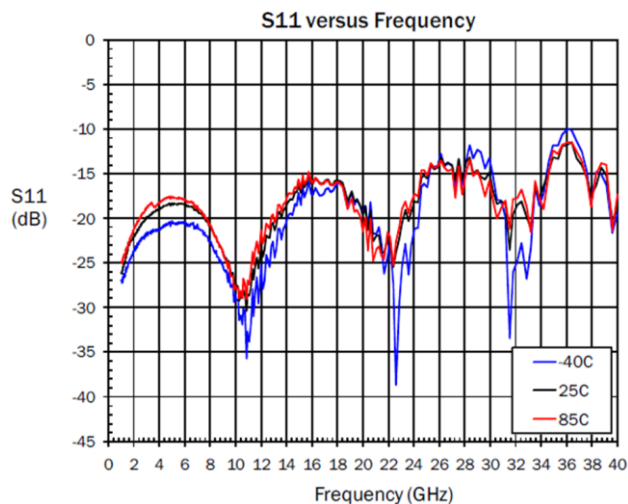
Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

Nominal Operating Parameters

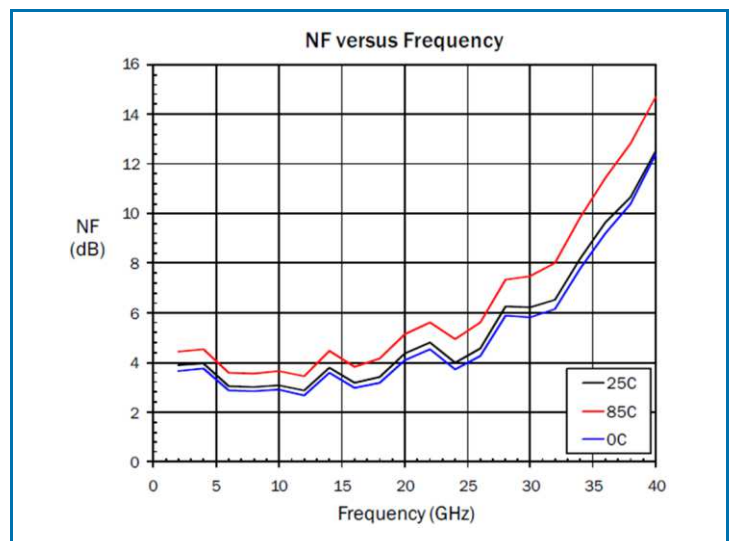
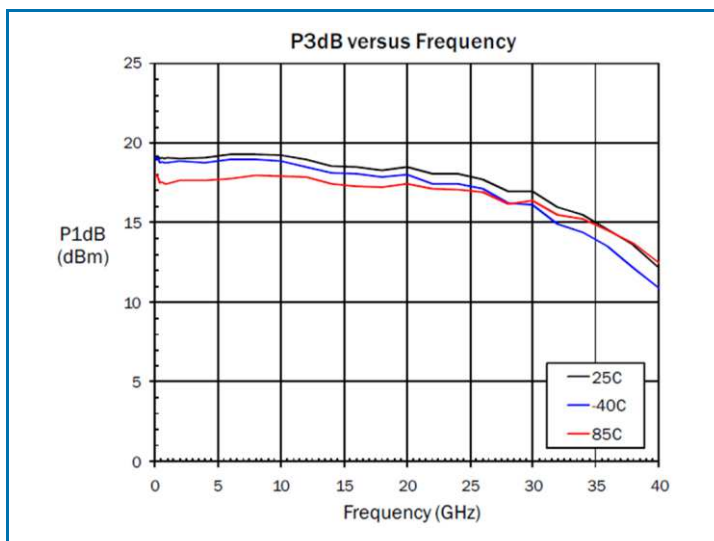
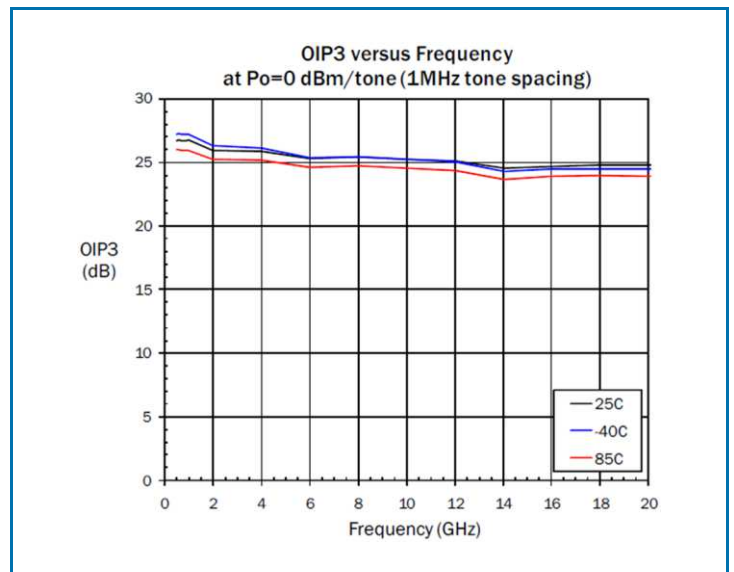
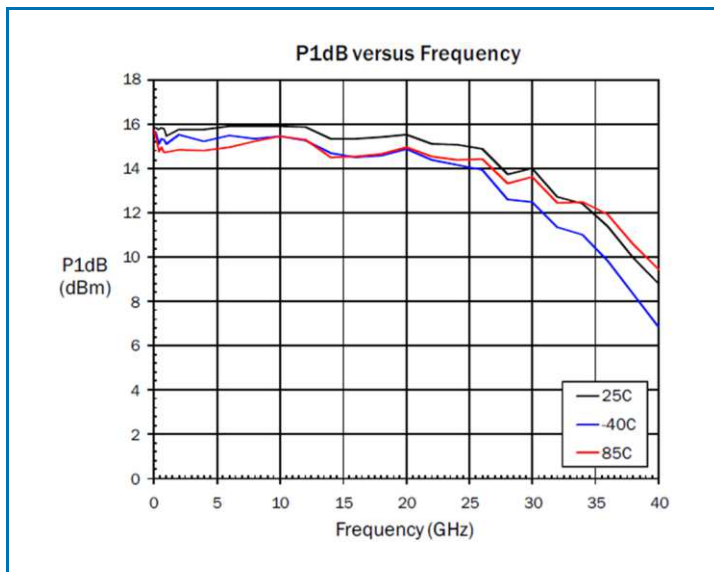
Parameter	Specification			Unit	Condition
	Min	Typ	Max		
General Performance					$T_A = +25^{\circ}\text{C}$, $V_{DD} = +8V_{DC}$, $V_{G2} = +1.5V_{DC}$, $I_{DD} = 100\text{mA}^*$
Operating Frequency	0		35	GHz	3dB BW
Gain	10.8	11.8		dB	20GHz
IP3		25		dBm	P_{OUT} 0dBm, 20GHz
P1dB		15		dBm	20GHz
P_{3dB}		17.5		dBm	20GHz
Noise Figure at Mid-Band		4		dB	20GHz
Input Return Loss		16		dB	
Output Return Loss		15			
Supply Current		100		mA	
Supply Voltage		6.5		V_{DC}	

*Adjust VTI between $-1.5V_{DC}$ to $+0.2V_{DC}$ to achieve $I_{DD} = 160\text{mA}$ typical., $V_{G2} = 2.75V_{DC}$

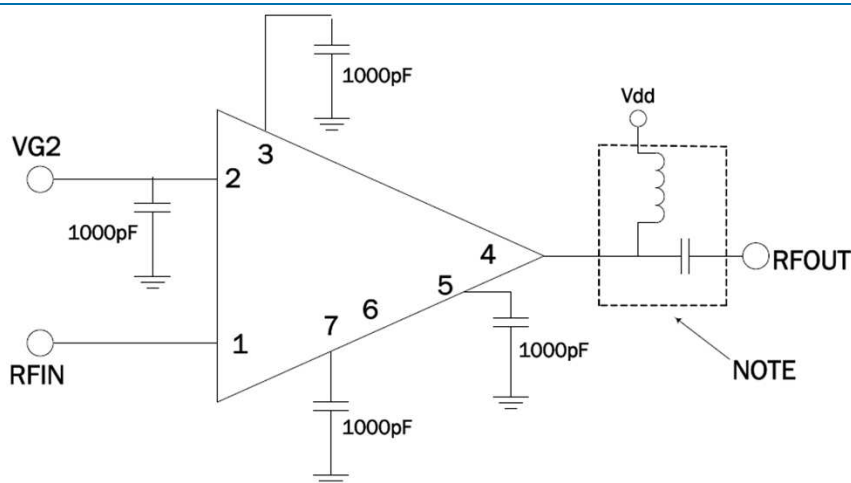
Typical Performance



Typical Performance (Continued)

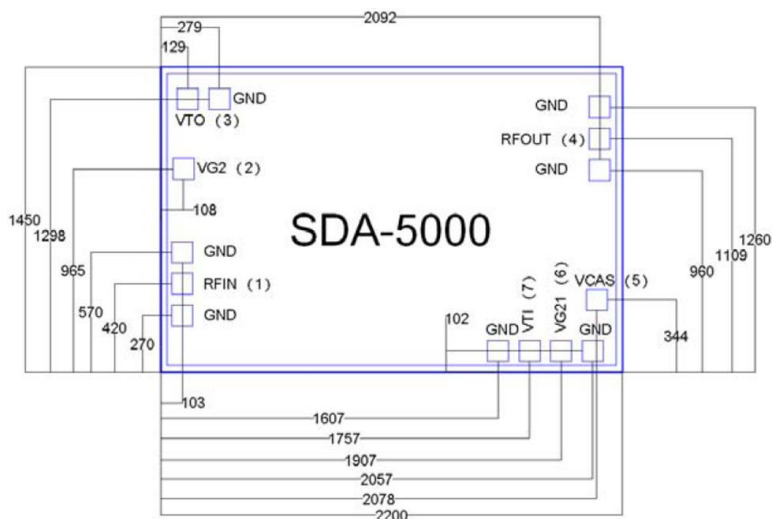


Application Schematic



NOTE: Drain Bias (V_{DD}) must be applied through a broadband bias tee or external bias network.

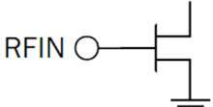
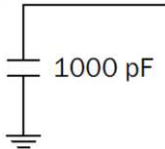
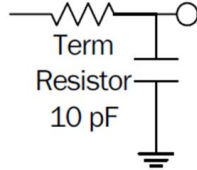
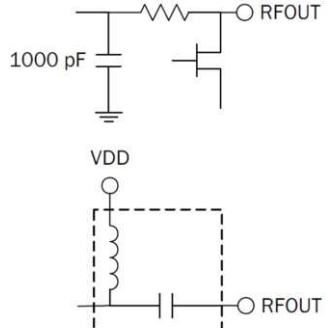
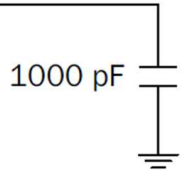
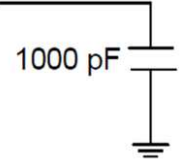
Die Drawing (Dimensions in millimeters)



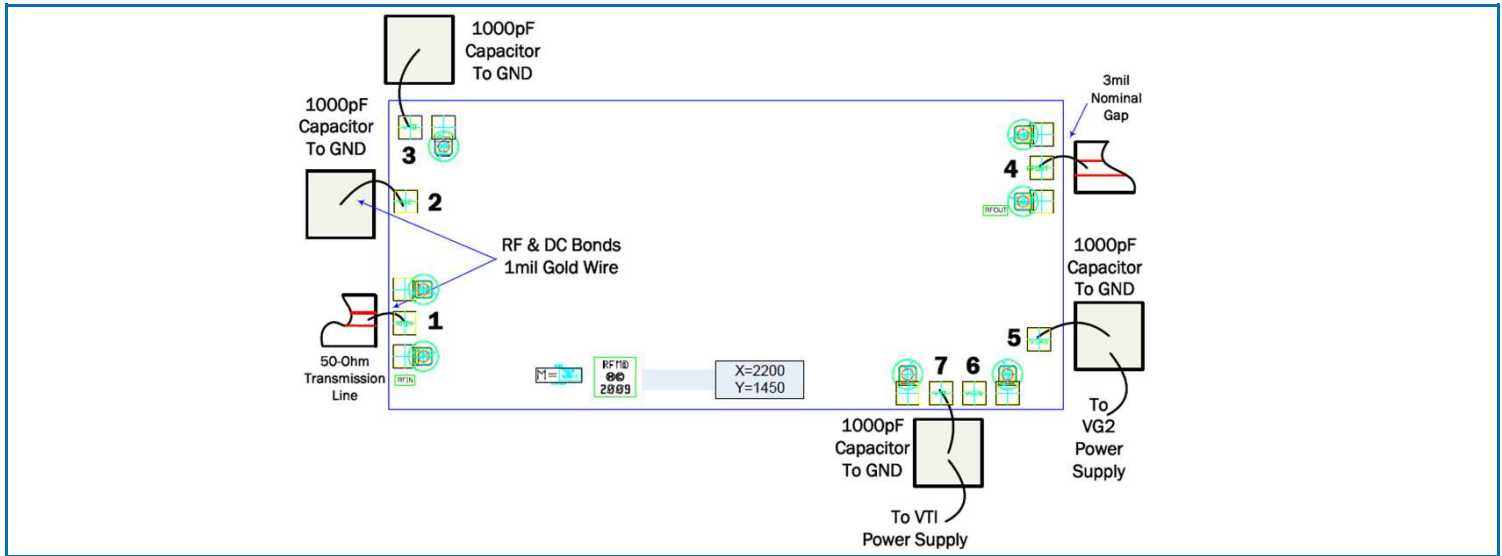
Notes:

1. No connection required for unlabeled bond pads
2. Die thickness is 0.102mm (4mil)
3. Typical bond pad is 0.100mm square
4. Backside metallization: gold
5. Backside metal is ground
6. Bond pad metallization: gold
7. Refer to drawing posted at www.rfmd.com for tolerances

Pin Names and Descriptions

Pin	Name	Description	Interface Schematic
1	RFIN	RF Input. This pad is DC coupled and matched to 50Ω from DC to 35GHz. 50Ω microstrip transmission line on 0.127mm (5mil) thick alumina thin film substrate is recommended for RF input and output.	
2	VG2	VG2 is an optional pad. It may be used to bias the cascode gate of the amplifier. If this port is used, a 1000pF bypass capacitor with the shortest wirebond length possible is recommended to prevent low frequency gain ripple.	
3	VTO	The output drain termination pad. This pad requires a suggested 1000pF bypass capacitor with the shortest wirebond length to prevent low frequency gain ripple. The value of the external capacitance limits the low frequency response of the amplifier.	
4	RFOUT and VDD	RF Output. 50Ω microstrip transmission line on 0.127mm (5mil) thick alumina thin film substrate is recommended for RF input and output. Connect the DC bias (V_{DD}) network to provide drain current (I_{DD}).	 <p>Note: Drain Bias (V_{DD}) must be applied through a broadband bias tee or external bias network</p>
5	VCAS	Provides VG2 gate voltage to the cascode amplifier. The value is $\sim (V_{CC}/2 - \text{absolute value of } V_{TI})$.	
6	VG21	Not connected.	
7	VTI	Input gate voltage, used to bias the amplifier. The value is between $-1.5V_{DC}$ (device is pinched OFF) to $+0.2V_{DC}$ (fully ON). This pad requires a bypass capacitor to ground with the shortest possible wirebond length to prevent low frequency gain ripple. The value of the external capacitance limits the low frequency response of the amplifier.	
Die	GND	Ground connection. Connect die bottom directly to ground plane for best performance. NOTE: The die should be connected directly to the ground plane with conductive epoxy.	

Assembly Diagram



Measurement Technique

All specifications and typical performances reported in this document were measured in the following manner. Data was taken using a temperature controlled probe station utilizing 150 μ m pitch GSG probes. The interface between the probes and integrated circuit was made with a coplanar to microstrip ceramic test interface. The test interface was then wire bonded to the die as shown in the figure below using 1 mil diameter bondwires. The spacing between the test interface and the die was 200 μ m, and the bond wire loop height was 100 μ m. The thickness of the test interface is 125 μ m (5mil). The calibration of the test fixture included the probes and test interfaces, so that the measurement reference plane was at the point of bond wire attachment. Therefore, all data represents the integrated circuit and accompanying bond wires.

